
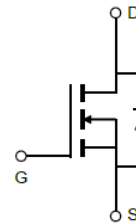
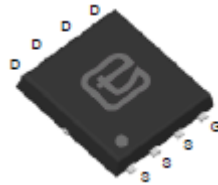


**40V N-Channel Trench MOSFET(Preliminary)**

<p>General Description</p> <ul style="list-style-type: none"> ● Trench Power technology ● Low $R_{DS(ON)}$ ● Low Gate Charge ● Optimized for fast-switching applications <p>Applications</p> <ul style="list-style-type: none"> ● Synchronous Rectification in DC/DC and AC/DC Converters ● Isolated DC/DC Converters in Telecom and Industrial 	<p>Product Summary</p> <table> <tr> <td>V_{DS}</td> <td>40V</td> </tr> <tr> <td>I_D (at $V_{GS}=10V$)</td> <td>120A</td> </tr> <tr> <td>$R_{DS(ON)}$ (at $V_{GS}=10V$)</td> <td>< 3.5mΩ</td> </tr> <tr> <td>$R_{DS(ON)}$ (at $V_{GS}=4.5V$)</td> <td>< 4.7mΩ</td> </tr> </table> <p>100% UIS Tested</p> 	V_{DS}	40V	I_D (at $V_{GS}=10V$)	120A	$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 3.5m Ω	$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 4.7m Ω
V_{DS}	40V								
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DFN5x6



Part Number	Package Type	Form	Marking
TTG120N04AT	DNF 5*6	Tape&Reel	120N04AT

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^B	I_D	$T_C = 25^\circ\text{C}$	51
		$T_C = 100^\circ\text{C}$	51
Pulsed Drain Current ^A	I_{DM}	360	A
Avalanche Current ^A	I_{AS}	35	A
Single Pulse Avalanche Energy $L = 0.3\text{mH}$ ^A	E_{AS}	138.4	mJ
Power Dissipation ^C	P_D	$T_C = 25^\circ\text{C}$	143
		$T_C = 100^\circ\text{C}$	82
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Case	$R_{\theta JC}$	1.1	$^\circ\text{C/W}$
Maximum Junction-to-Ambient			
	$R_{\theta JA}$	100	



Electrical Characteristics($T_J = 25^\circ\text{C}$ unless otherwise noted)						
Symbol	Parameter	Conditions	Value			Units
			Min	Typ	Max	
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	40			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 40\text{V}, V_{GS} = 0\text{V}$	$T_J = 25^\circ\text{C}$		1	μA
			$T_J = 100^\circ\text{C}$		25	
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1	1.7	2.4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{V}, I_D = 30\text{A}$		2.7	3.5	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 30\text{A}$		3.6	4.7	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{V}, I_D = 20\text{A}$		36.4		S
V_{SD}	Diode Forward Voltage	$I_S = 30\text{A}, V_{GS} = 0\text{V}$			1	V
I_S	Maximum Body-Diode Continuous Current ^B				51	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 20\text{V}, f = 1\text{MHz}$		5331		pF
C_{oss}	Output Capacitance			987		
C_{rss}	Reverse Transfer Capacitance			378		
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS} = 10\text{V}, V_{DS} = 20\text{V}, I_D = 30\text{A}$		132		nC
Q_{gs}	Gate Source Charge			23		
Q_{gd}	Gate Drain Charge			23		
$t_{D(on)}$	Turn-On Delay Time	$V_{GS} = 10\text{V}, V_{DS} = 20\text{V}, I_D = 30\text{A}, R_G = 3\Omega$		27		ns
t_r	Turn-On Rise Time			11		
$T_{D(off)}$	Turn-Off Delay Time			83		
t_f	Turn-Off Fall Time			14		
t_{rr}	Body Diode Reverse Recovery Time	$I_F = 20\text{A}, di/dt = 100\text{A}/\mu\text{s}$		66		ns
Q_{rr}	Body Diode Reverse Recovery Charge			73		nC

A. Single pulse width limited by maximum junction temperature.

B. The maximum current rating is package limited.

C. The power dissipation P_D is based on $T_{J(MAX)} = 175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

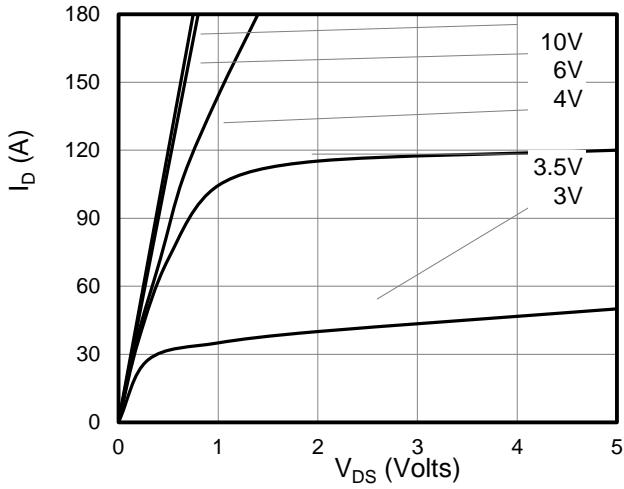


Figure 1: On-Region Characteristics

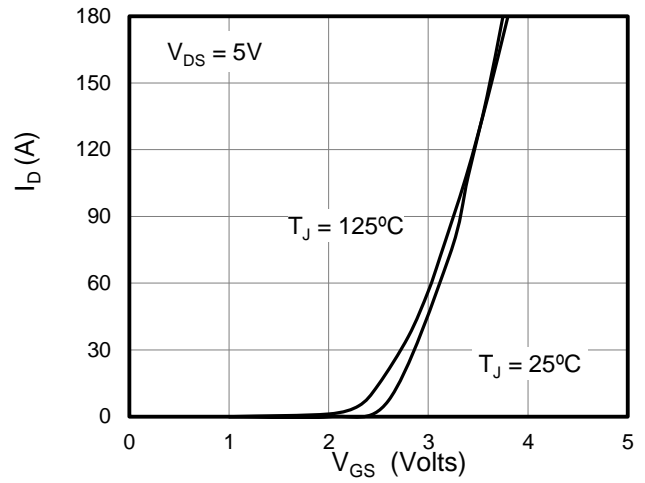


Figure 2: Transfer Characteristics

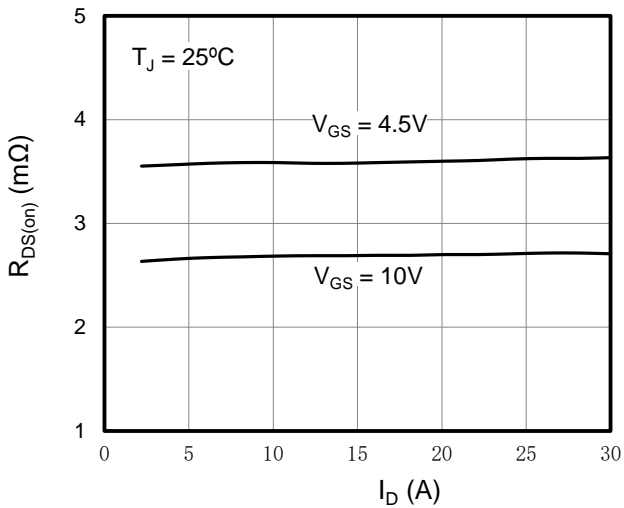


Figure 3: On-Resistance vs. Drain Current

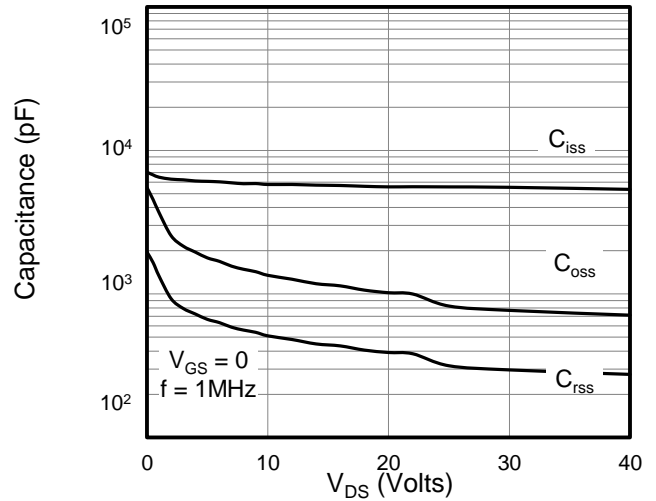


Figure 4: Capacitance Characteristics

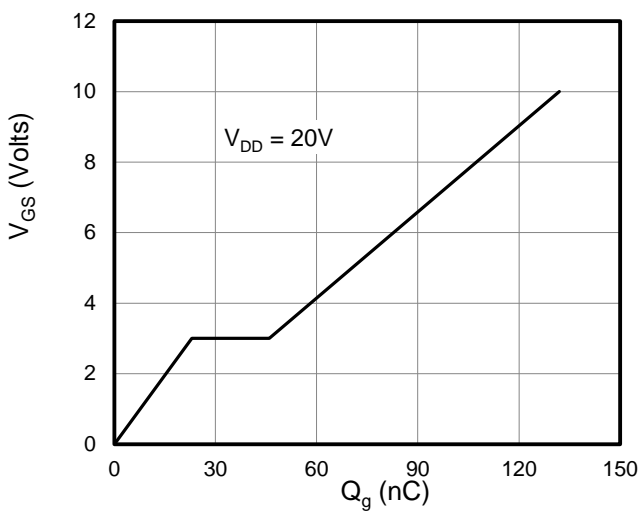


Figure 5: Gate Charge Characteristics

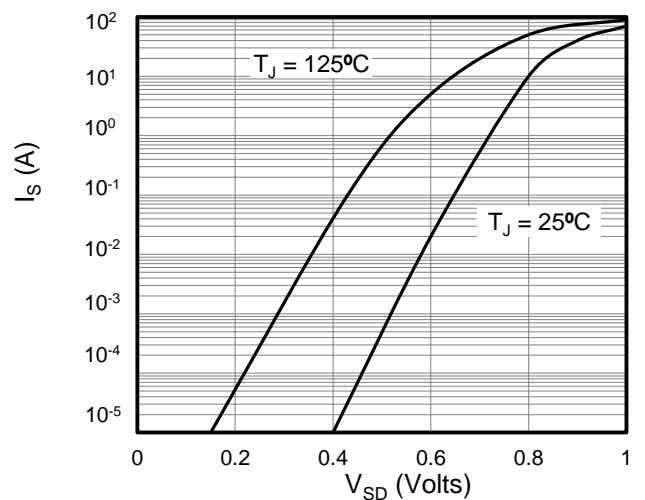


Figure 6: Body Diode Forward Voltage



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

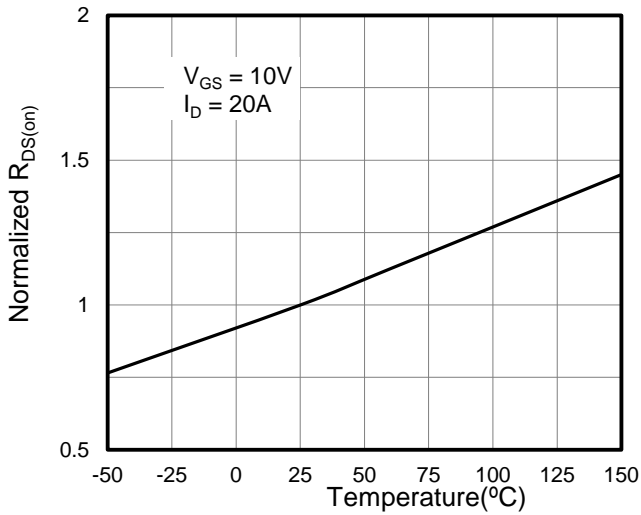


Figure 7: On-Resistance vs. Junction Temperature

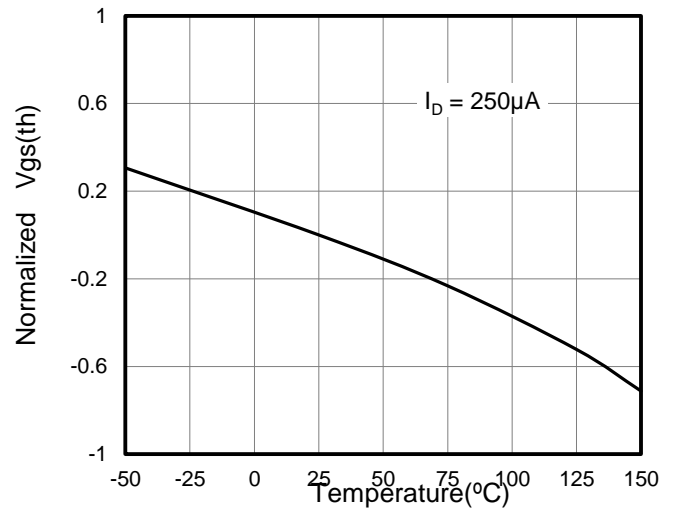


Figure 8: $V_{GS(th)}$ vs. Junction Temperature

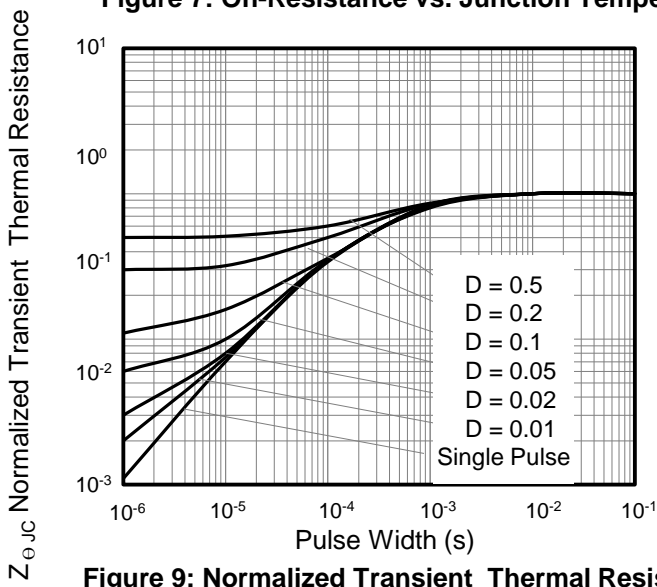


Figure 9: Normalized Transient Thermal Resistance

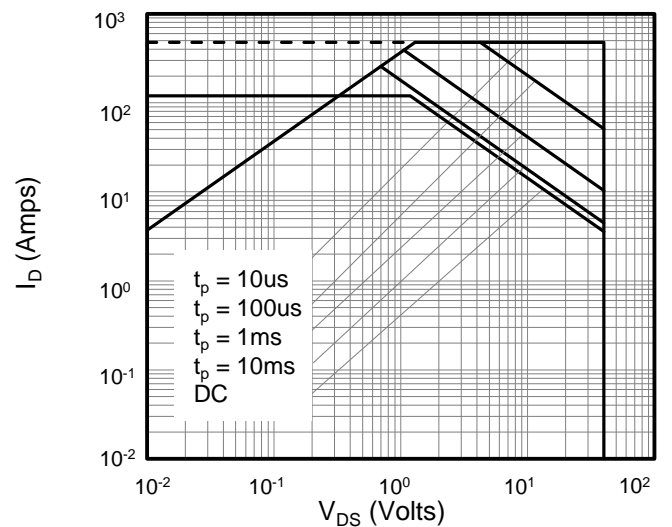


Figure 10: Safe Operating Area

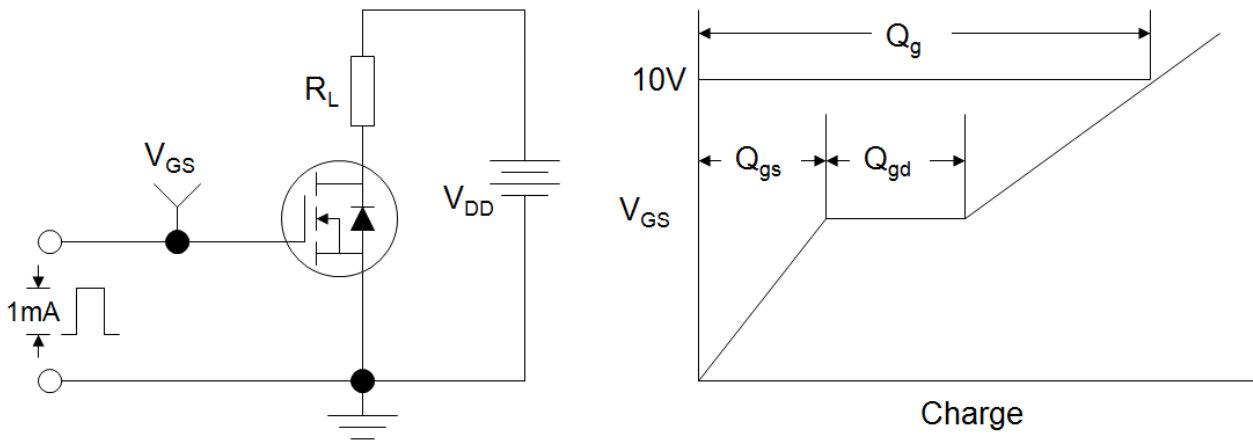


Figure A: Gate Charge Test Circuit and Waveforms

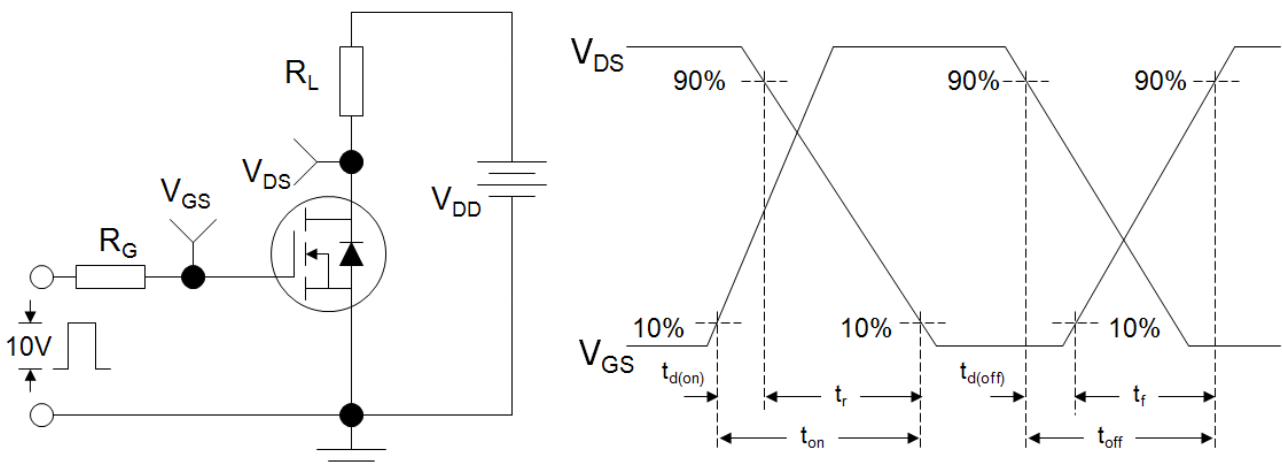


Figure B: Resistive Switching Test Circuit and Waveforms

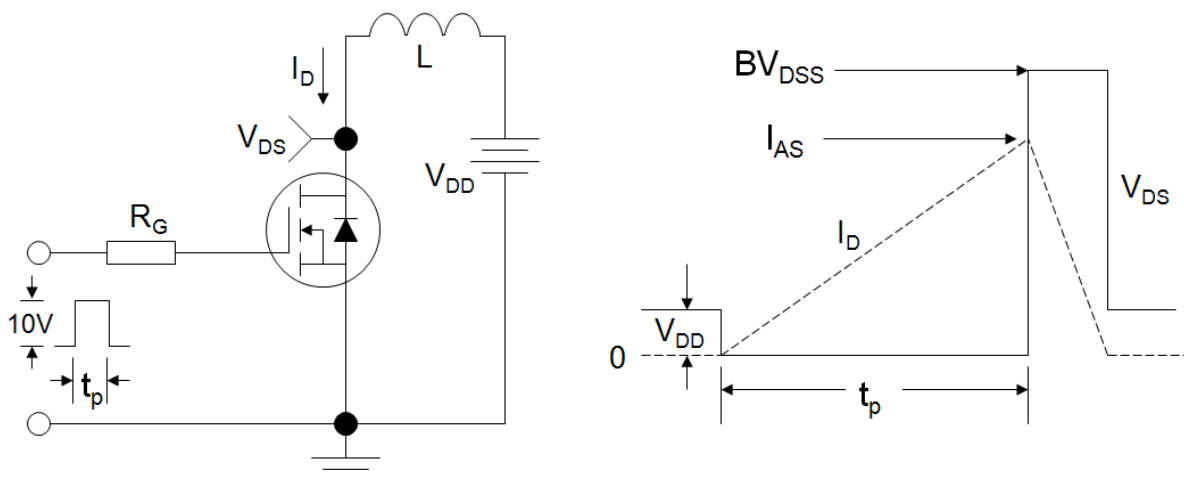
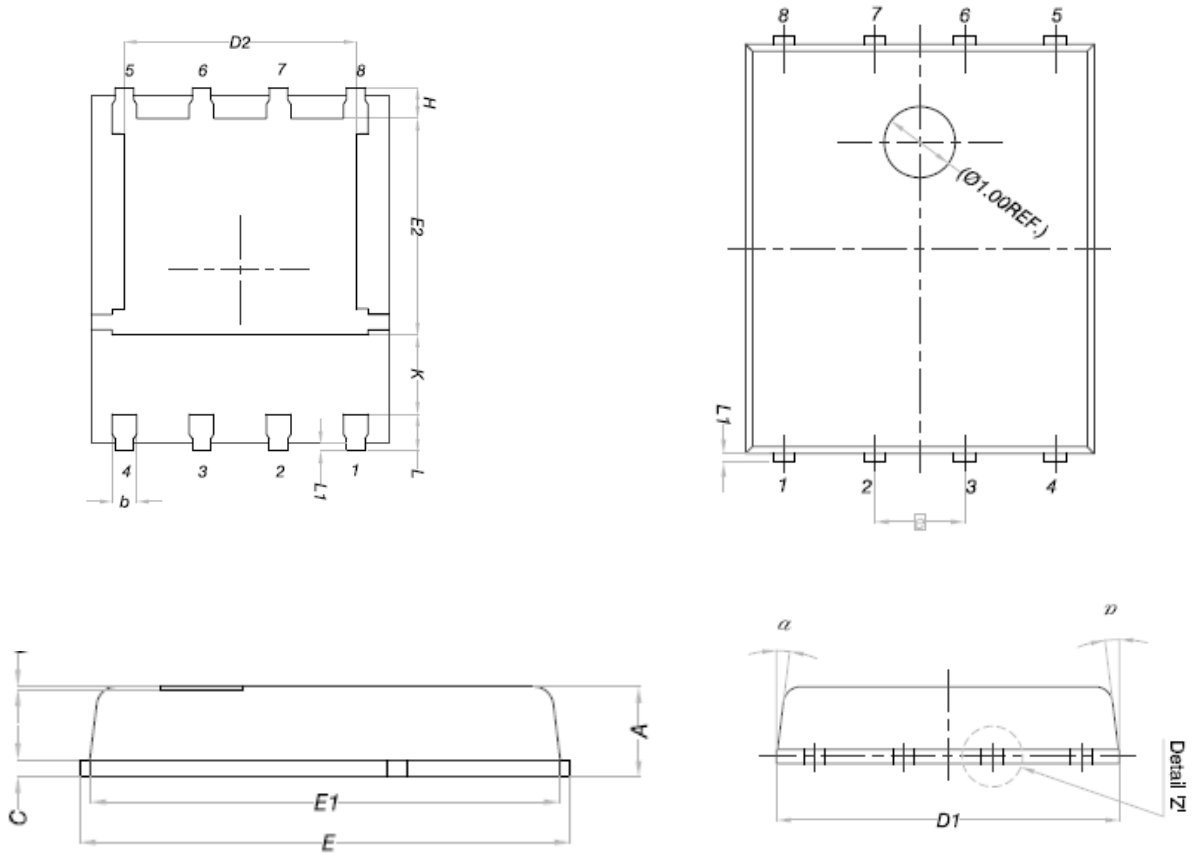


Figure C: Unclamped Inductive Switching (UIS) Test Circuit and Waveforms



DFN5x6(捷敏)



DIM.	MILLIMETERS			DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.		MIN.	NOM.	MAX.
A	0.90	1.00	1.10	E	5.90	6.00	6.10
A1	0	-	0.05	E1	5.70	5.75	5.80
b	0.33	0.41	0.51	E2	3.38	3.58	3.78
C	0.20	0.25	0.30	e	1.27 BSC		
D1	4.80	4.90	5.00	H	0.41	0.51	0.61
D2	3.61	3.81	3.96	K	1.10	-	-
				L	0.51	0.61	0.71
				L1	0.06	0.13	0.20
				α	0°	-	12°



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